

# Ran Yu

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11812522/publications.pdf>

Version: 2024-02-01

30  
papers

1,189  
citations

516710

16  
h-index

580821

25  
g-index

31  
all docs

31  
docs citations

31  
times ranked

859  
citing authors

#	ARTICLE	IF	CITATIONS
1	Detection of ultra-low protein concentrations with the simplest possible field effect transistor. <i>Nanotechnology</i> , 2019, 30, 324001.	2.6	12
2	Junctionless nanowire transistor fabricated with high mobility Ge channel. <i>Physica Status Solidi - Rapid Research Letters</i> , 2014, 8, 65-68.	2.4	16
3	Component design and testing for a miniaturised autonomous sensor based on a nanowire materials platform. <i>Microsystem Technologies</i> , 2014, 20, 971-988.	2.0	1
4	Fully CMOS-compatible top-down fabrication of sub-50nm silicon nanowire sensing devices. <i>Microelectronic Engineering</i> , 2014, 118, 47-53.	2.4	14
5	Optimized Laser Thermal Annealing on Germanium for High Dopant Activation and Low Leakage Current. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 4047-4055.	3.0	39
6	Access resistance reduction in Ge nanowires and substrates based on non-destructive gas-source dopant in-diffusion. <i>Journal of Materials Chemistry C</i> , 2014, 2, 9248-9257.	5.5	18
7	Atomically Flat Low-Resistive Germanide Contacts Formed by Laser Thermal Anneal. <i>IEEE Transactions on Electron Devices</i> , 2013, 60, 2178-2185.	3.0	22
8	Functionalized 3D 7&#x00D7;20-array of vertically stacked SiNW FET for streptavidin sensing. , 2013, , .		2
9	Resistâ€“substrate interface tailoring for generating high-density arrays of Ge and Bi <sub>2</sub> Se <sub>3</sub> nanowires by electron beam lithography. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012, 30, .	1.2	17
10	Influence of channel material properties on performance of nanowire transistors. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	24
11	Bipolar effects in unipolar junctionless transistors. <i>Applied Physics Letters</i> , 2012, 101, 093507.	3.3	39
12	Emission and absorption of optical phonons in Multigate Silicon Nanowire MOSFETs. <i>Journal of Computational Electronics</i> , 2012, 11, 249-265.	2.5	16
13	Intrinsic gate delay and energy-delay product in junctionless nanowire transistors. , 2012, , .		6
14	Electron transport in germanium junctionless nanowire transistors. , 2012, , .		0
15	Device Design and Estimated Performance for p-Type Junctionless Transistors on Bulk Germanium Substrates. <i>IEEE Transactions on Electron Devices</i> , 2012, 59, 2308-2313.	3.0	31
16	Influence of discrete dopant on quantum transport in silicon nanowire transistors. <i>Solid-State Electronics</i> , 2012, 70, 92-100.	1.4	15
17	Improvement of carrier ballisticity in junctionless nanowire transistors. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	43
18	Characterization of a junctionless diode. <i>Applied Physics Letters</i> , 2011, 99, 013502.	3.3	6

#	ARTICLE	IF	CITATIONS
19	Nanowire to Single-Electron Transistor Transition in Trigate SOI MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 26-32.	3.0	9
20	Influence of Elastic and Inelastic Electron-Phonon Interaction on Quantum Transport in Multigate Silicon Nanowire MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 1029-1037.	3.0	9
21	Junctionless Multiple-Gate Transistors for Analog Applications. IEEE Transactions on Electron Devices, 2011, 58, 2511-2519.	3.0	234
22	A Simulation Comparison between Junctionless and Inversion-Mode MuGFETs. ECS Transactions, 2011, 35, 63-72.	0.5	29
23	Junctionless Nanowire Transistor: Complementary Metal-Oxide-Semiconductor Without Junctions. Science of Advanced Materials, 2011, 3, 477-482.	0.7	36
24	Effect of intravalley acoustic phonon scattering on quantum transport in multigate silicon nanowire metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2010, 108, 034510.	2.5	19
25	Fabrication of Germanium-on-Insulator by low temperature direct wafer bonding. , 2010, , .		6
26	Reduced electric field in junctionless transistors. Applied Physics Letters, 2010, 96, 073510.	3.3	269
27	Mobility improvement in nanowire junctionless transistors by uniaxial strain. Applied Physics Letters, 2010, 97, .	3.3	38
28	Low subthreshold slope in junctionless multigate transistors. Applied Physics Letters, 2010, 96, .	3.3	195
29	Nanowire zero-capacitor DRAM transistors with and without junctions. , 2010, , .		17
30	Dissipative transport in Multigate silicon nanowire transistors. , 2010, , .		4